

Infineon® LITIXTM Basic

TLD1121EL

1 Channel High Side Current Source

Data Sheet

Rev. 1.1, 2015-03-19

Automotive

TLD1121EL



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1 Channel High Side Current Source LITIX[™] Basic

TLD1121EL





1 Overview

Features

- 1 Channel device with integrated output stage (current source), optimized to drive LEDs
- · Output current up to 360mA
- · Low current consumption in sleep mode
- PWM-operation supported via VS- and EN-pin
- Output current adjustable via external low power resistor and possibility to connect PTC resistor for LED protection during over temperature conditions
- Reverse polarity protection
- Overload protection
- Undervoltage detection
- · Open load and short circuit to GND diagnosis
- Wide temperature range: -40 °C < T_i < 150 °C
- PG-SSOP14 package with exposed heatslug
- Green Product (RoHS compliant)
- AEC Qualified



PG-SSOP14

Description

The LITIXTM Basic TLD1121EL is a one channel high side driver IC with integrated output stage. It is designed to control LEDs with a current up to 360 mA. In typical automotive applications the device is capable to drive i.e. 3 red LEDs with a current up to 180 mA, which is limited by thermal cooling aspects. The output current is controlled practically independent of load and supply voltage changes.

Table 1 Product Summary

Operating voltage	$V_{S(nom)}$	5.5 V 40 V
Maximum voltage	$V_{ m S(max)} \ V_{ m OUT(max)}$	40 V
Nominal output (load) current	$I_{OUT(nom)}$	180 mA when using a supply voltage range of 8V - 18V (e.g. Automotive car battery). Currents up to $I_{\rm OUT(max)}$ possible in applications with low thermal resistance $R_{\rm thJA}$
Maximum output (load) current	$I_{OUT(max)}$	360 mA; depending on thermal resistance $R_{\rm thJA}$
Output current accuracy at $R_{\rm SET}$ = 12 k Ω	k_{LT}	2250 ± 7%
Current consumption in sleep mode	$I_{S(sleep,typ)}$	0.1 μΑ

Туре	Package	Marking
TLD1121EL	PG-SSOP14	TLD1121EL

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Overview

Protective functions

- ESD protection
- Under voltage lock out
- Over Load protection
- Over Temperature protection
- Reverse Polarity protection

Diagnostic functions

- OL detection
- SC to Vs (indicated by OL diagnosis)
- SC to GND detection

Applications

Designed for exterior LED lighting applications such as tail/brake light, turn indicator, position light, side marker,... The device is also well suited for interior LED lighting applications such as ambient lighting, interior illumination and dash board lighting.



Block Diagram

2 Block Diagram

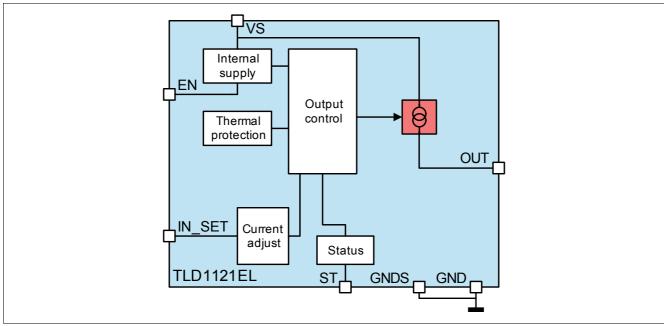


Figure 1 Basic Block Diagram



Pin Configuration

3 Pin Configuration

3.1 Pin Assignment

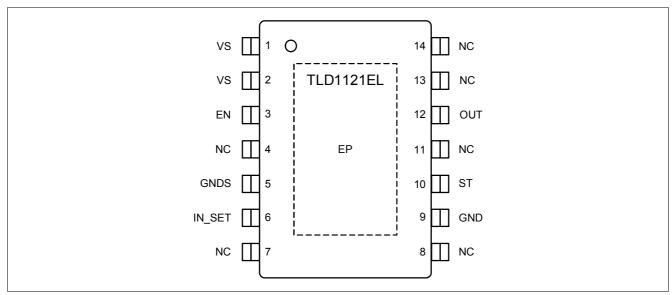


Figure 2 Pin Configuration



Pin Configuration

3.2 Pin Definitions and Functions

Pin	Symbol	Input/ Output	Function
1, 2	VS	_	Supply Voltage; battery supply, connect a decoupling capacitor (100 nF - 1 μ F) to GND
3	EN	I	Enable pin
4	NC	_	Pin not connected
5	GNDS	_	1) GNDS ; Signal GND, connect to GND
6	IN_SET	I/O	Input / SET pin; Connect a low power resistor to adjust the output current
7	NC	_	Pin not connected
8	NC	_	Pin not connected
9	GND	_	1) Ground
10	ST	I/O	Status pin
11	NC	_	Pin not connected
12	OUT	0	Output
13	NC	_	Pin not connected
14	NC	_	Pin not connected
Exposed Pad	GND	_	1) Exposed Pad; connect to GND in application

¹⁾ Connect all GND-pins together.



General Product Characteristics

4 General Product Characteristics

4.1 Absolute Maximum Ratings

Absolute Maximum Ratings 1)

 $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit	Values	Unit	Conditions	
			Min.	Max.			
Voltage	s		+	+			
4.1.1	Supply voltage	V_{S}	-16	40	V	_	
4.1.2	Input voltage EN	V_{EN}	-16	40	V	_	
4.1.3	Input voltage EN related to $V_{\rm S}$	$V_{EN(VS)}$	V _S - 40	V _S + 16	V	_	
4.1.4	Input voltage EN related to $V_{\rm OUT}$ $V_{\rm EN}$ - $V_{\rm OUT}$	V_{EN} - V_{OUT}	-16	40	V	_	
4.1.5	Output voltage	V_{OUT}	-1	40	V	_	
4.1.6	Power stage voltage $V_{PS} = V_S - V_{OUT}$	V_{PS}	-16	40	V	_	
4.1.7	IN_SET voltage	V_{IN_SET}	-0.3	6	V	_	
4.1.8	Status voltage	$V_{\rm ST}$	-0.3	6	V	_	
Current	s	<u> </u>	1				
4.1.9	IN_SET current	I_{IN_SET}	_ _	2 8	mA	– Diagnosis output	
4.1.10	Output current	I_{OUT}	_	390	mA	_	
Temper	atures		- 11	1			
4.1.11	Junction temperature	T_{i}	-40	150	°C	_	
4.1.12	Storage temperature	T_{stg}	-55	150	°C	_	
ESD Su	sceptibility						
4.1.13	ESD resistivity to GND	V_{ESD}	-2	2	kV	Human Body Model (100 pF via $1.5 \text{ k}\Omega)^{2)}$	
4.1.14	ESD resistivity all pins to GND	V_{ESD}	-500	500	V	CDM ³⁾	
4.1.15	ESD resistivity corner pins to GND	V_{ESD}	-750	750	V	CDM ³⁾	

¹⁾ Not subject to production test, specified by design

Note: Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

²⁾ ESD susceptibility, Human Body Model "HBM" according to ANSI/ESDA/JEDEC JS-001-2011

³⁾ ESD susceptibility, Charged Device Model "CDM" according to JESD22-C101E



General Product Characteristics

4.2 Functional Range

Pos.	Parameter	Symbol	Lim	Limit Values		Conditions	
			Min.	Max.			
4.2.16	Supply voltage range for normal operation	$V_{\mathrm{S(nom)}}$	5.5	40	V	_	
4.2.17	Power on reset threshold	$V_{\mathrm{S(POR)}}$	_	5	V	$\begin{split} V_{\text{EN}} &= V_{\text{S}} \\ R_{\text{SET}} &= 12 \text{ k}\Omega \\ I_{\text{OUT}} &= 80\% \ I_{\text{OUT(nom)}} \\ V_{\text{OUT}} &= 2.5 \text{ V} \end{split}$	
4.2.18	Junction temperature	T_{j}	-40	150	°C	_	

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

4.3 Thermal Resistance

Pos.	Parameter	Symbol		Limit Val	ues	Unit	Conditions
			Min.	Тур.	Max.		
4.3.1	Junction to Case	R_{thJC}	_	8	10	K/W	1) 2)
4.3.2	Junction to Ambient 1s0p board	R_{thJA1}				K/W	1) 3)
			_	61	_		$T_{\rm a}$ = 85 °C
			_	56	-		$T_{\rm a}$ = 135 °C
4.3.3	Junction to Ambient 2s2p board	R_{thJA2}				K/W	1) 4)
			_	45	_		$T_{\rm a}$ = 85 °C
			_	43	_		$T_{\rm a}$ = 135 °C

¹⁾ Not subject to production test, specified by design. Based on simulation results.

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²⁾ Specified $R_{\rm thJC}$ value is simulated at natural convection on a cold plate setup (all pins and the exposed Pad are fixed to ambient temperature). $T_{\rm a}$ = 85°C, Total power dissipation 1.5 W.

³⁾ The $R_{\rm thJA}$ values are according to Jedec JESD51-3 at natural convection on 1s0p FR4 board. The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5 mm³ board with 70µm Cu, 300 mm² cooling area. Total power dissipation 1.5 W distributed statically and homogenously over power stage.

⁴⁾ The R_{thJA} values are according to Jedec JESD51-5,-7 at natural convection on 2s2p FR4 board. The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5 mm³ board with 2 inner copper layers (outside 2 x 70 μ m Cu, inner 2 x 35 μ m Cu). Where applicable, a thermal via array under the exposed pad contacted the first inner copper layer. Total power dissipation 1.5 W distributed statically and homogenously over power stage.



5 EN Pin

The EN pin is a dual function pin:

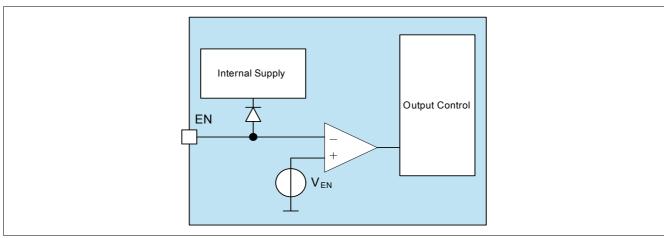


Figure 3 Block Diagram EN pin

Note: The current consumption at the EN-pin $I_{\rm EN}$ needs to be added to the total device current consumption. The total current consumption is the sum of the currents at the VS-pin $I_{\rm S}$ and the EN-pin $I_{\rm EN}$.

5.1 EN Function

If the voltage at the pin EN is below a threshold of $V_{\rm EN(off)}$ the LITIXTM Basic IC will enter Sleep mode. In this state all internal functions are switched off, the current consumption is reduced to $I_{\rm S(sleep)}$. A voltage above $V_{\rm EN(on)}$ at this pin enables the device after the Power on reset time $t_{\rm POR}$.

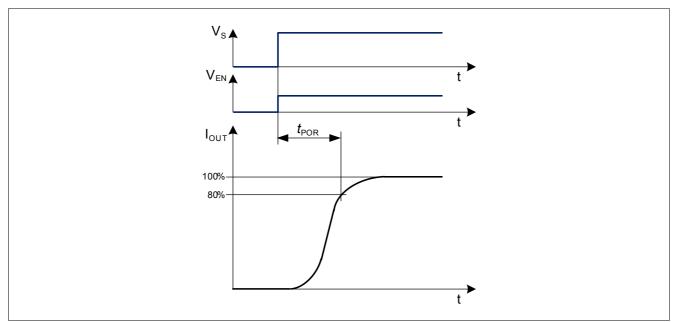


Figure 4 Power on reset



5.2 Internal Supply Pin

The EN pin can be used to supply the internal logic. There are two typical application conditions, where this feature can be used:

- 1) In "DC/DC control Buck" configurations, where the voltage $V_{\rm s}$ can be below 5.5V.
- 2) In configurations, where a PWM signal is applied at the Vbatt pin of a light module. The buffer capacitor $C_{\rm BUF}$ is used to supply the LITIXTM Basic IC during Vbatt low ($V_{\rm s}$ low) periods. This feature can be used to minimize the turn-on time to the values specified in **Pos. 9.2.13**. Otherwise, the power-on reset delay time $t_{\rm POR}$ (**Pos. 5.4.7**) has to be considered.

The capacitor can be calculated using the following formula:

$$C_{\text{BUF}} = t_{\text{LOW(max)}} \cdot \frac{I_{\text{EN(LS)}}}{V_{\text{S}} - V_{\text{D1}} - V_{\text{S(POR)}}} \tag{1}$$

See also a typical application drawing in Chapter 10.

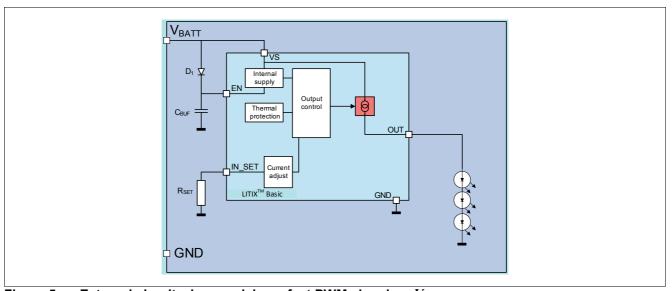


Figure 5 External circuit when applying a fast PWM signal on V_{BATT}



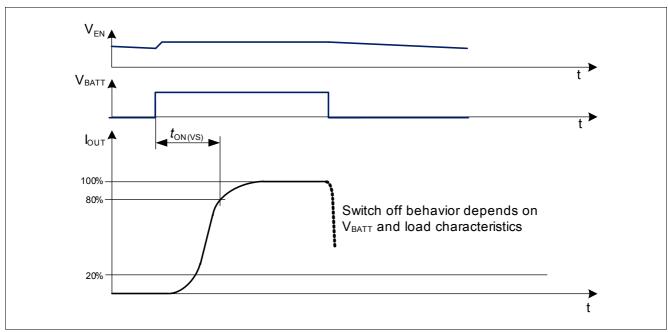


Figure 6 Typical waveforms when applying a fast PWM signal on V_{BATT}

The parameter $t_{ON(VS)}$ is defined at Pos. 9.2.13. The parameter $t_{OFF(VS)}$ depends on the load and supply voltage V_{BATT} characteristics.

5.3 EN Unused

In case of an unused EN pin, there are two different ways to connect it:

5.3.1 EN - Pull Up to VS

The EN pin can be connected with a pull up resistor (e.g. 10 k Ω) to V_s potential. In this configuration the LITIXTM Basic IC is always enabled.

5.3.2 EN - Direct Connection to VS

The EN pin can be connected directly to the VS pin (IC always enabled). This configuration has the advantage (compared to the configuration described in **Chapter 5.3.1**) that no additional external component is required.



5.4 Electrical Characteristics Internal Supply / EN Pin

Electrical Characteristics Internal Supply / EN pin

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Тур.	Max.		
5.4.1	Current consumption, sleep mode	$I_{\mathrm{S(sleep)}}$	_	0.1	2	μΑ	$^{1)}$ $V_{\rm EN}$ = 0.5 V $T_{\rm j}$ < 85 °C $V_{\rm S}$ = 18 V $V_{\rm OUT}$ = 3.6 V
5.4.2	Current consumption, active mode	$I_{S(on)}$	- - -	- - -	1.4 0.75 1.5	mA	$I_{\rm IN_SET} = 0~\mu{\rm A}$ $T_{\rm j} < 105~{\rm ^{\circ}C}$ $V_{\rm S} = 18~{\rm V}$ $V_{\rm OUT} = 3.6{\rm V}$ $V_{\rm EN} = 5.5~{\rm V}$ $V_{\rm EN} = 18~{\rm V}$ $^{1)}R_{\rm EN} = 10~{\rm k}\Omega$ between VS and EN-pin
5.4.3	Current consumption, device disabled via ST	$I_{\mathrm{S(dis,ST)}}$	- - -	- - -	1.4 0.65 1.4	mA	$^{2)}$ $V_{\rm S}$ = 18 V $T_{\rm j}$ < 105 °C $V_{\rm ST}$ = 5 V $V_{\rm EN}$ = 5.5 V $V_{\rm EN}$ = 18 V $^{1)}$ $R_{\rm EN}$ = 10 kΩ between VS and EN-pin
5.4.4	Current consumption, device disabled via IN_SET	$I_{\rm S(dis,IN_SET)}$	- - -	- - -	1.4 0.7 1.4	mA	$^{2)}$ $V_{\rm S}$ = 18 V $T_{\rm j}$ < 105 °C $V_{\rm IN_SET}$ = 5 V $V_{\rm EN}$ = 5.5 V $V_{\rm EN}$ = 18 V $^{1)}$ $R_{\rm EN}$ = 10 kΩ between VS and EN-pin
5.4.5	Current consumption, active mode in fault detection condition with ST- pin unconnected	$I_{\mathrm{S(fault,STu)}}$	_ _ _	- - -	1.7 1.1 1.8	mA	$^{2)}$ $V_{\rm S}$ = 18 V $T_{\rm j}$ < 105 °C $R_{\rm SET}$ = 12 kΩ $V_{\rm OUT}$ = 18 V or 0 V $V_{\rm EN}$ = 5.5 V $V_{\rm EN}$ = 18 V $^{1)}$ $R_{\rm EN}$ = 10 kΩ between VS and EN-pin



Electrical Characteristics Internal Supply / EN pin (cont'd)

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Val	ues	Unit	Conditions
			Min.	Тур.	Max.		
5.4.6	Current consumption,	$I_{\rm S(fault,STG)}$				mA	$^{2)} V_{\rm S}$ = 18 V
	active mode in fault	S(iddit,S:S)					T _i < 105 °C
	detection condition with ST-						R'_{SET} = 12 k Ω
	pin connected to GND						V_{OUT} = 18 V or 0 V
							$V_{\rm ST}$ = 0 V
			_	_	6.0		$V_{\rm EN}$ = 5.5 V
			_	_	4.9		V_{EN} = 18 V
			_	_	5.9		$^{1)}R_{\rm EN}$ = 10 k Ω between
							VS and EN-pin
5.4.7	Power-on reset delay time 3)	t_{POR}	_	_	25	μs	$^{1)}$ $V_{\rm S}$ = $V_{\rm EN}$ = 0 \rightarrow 13.5 V
							$V_{\rm OUT(nom)}$ = 3.6 ± 0.3V
							I_{OUT} = 80% $I_{\text{OUT(nom)}}$
5.4.8	Required supply voltage for	$V_{S(on)}$	_	_	4	V	V _{EN} = 5.5 V
	output activation	O(OII)					V_{OUT} = 3 V
							$I_{\rm OUT}$ = 50% $I_{\rm OUT(nom)}$
5.4.9	Required supply voltage for	$V_{S(CC)}$	_	_	5.2	V	V _{EN} = 5.5 V
	current control	0(00)					$V_{\rm OUT}$ = 3.6 V
							$I_{OUT} \geq 90\% \ I_{OUT(nom)}$
5.4.10	EN turn on threshold	$V_{EN(on)}$	_	_	2.5	V	_
5.4.11	EN turn off threshold	$V_{EN(off)}$	0.8	_	_	V	_
5.4.12	EN input current during low	$I_{EN(LS)}$	_	_	1.8	mA	$^{1)} V_{\rm S} = 4.5 \rm V$
	supply voltage	LIN(LO)					T _i < 105 °C
							$V_{\rm EN}$ = 5.5 V
5.4.13	EN high input current	$I_{EN(H)}$				mA	<i>T</i> _i < 105 °C
		(/	_	_	0.1		$V_{\rm S}$ = 13.5 V, $V_{\rm EN}$ = 5.5 V
			_	-	0.1		$V_{\rm S}$ = 18 V, $V_{\rm EN}$ = 5.5 V
			_	_	1.65		$V_{\rm S} = V_{\rm EN} = 18 {\rm V}$
			_	-	0.45		$^{1)} V_{\rm S}$ = 18 V, $R_{\rm EN}$ = 10 k Ω
							between VS and EN-pin

¹⁾ Not subject to production test, specified by design

²⁾ The total device current consumption is the sum of the currents $I_{\rm S}$ and $I_{\rm EN(H)}$, please refer to Pos. 5.4.13

³⁾ See also Figure 4



IN_SET Pin

6 IN_SET Pin

The IN_SET pin is a multiple function pin for output current definition, input and diagnostics:

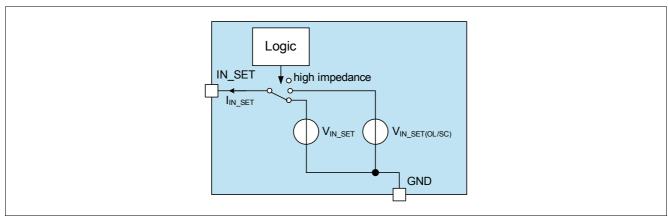


Figure 7 Block Diagram IN_SET pin

6.1 Output Current Adjustment via RSET

The current adjustment can be done by placing a low power resistor (R_{SET}) at the IN_SET pin to ground. The dimensioning of the resistor can be done using the formula below:

$$R_{\text{SET}} = \frac{k}{I_{\text{OUT}}} \tag{2}$$

The gain factor k ($R_{\rm SET}$ * output current) is specified in **Pos. 9.2.4** and **Pos. 9.2.5**. The current through the $R_{\rm SET}$ is defined by the resistor itself and the reference voltage $V_{\rm IN_SET(ref)}$, which is applied to the IN_SET during supplied device.

6.2 Smart Input Pin

The IN_SET pin can be connected via $R_{\rm SET}$ to the open-drain output of a $\mu \rm C$ or to an external NMOS transistor as described in Figure 8. This signal can be used to turn off the output stage of the IC. A minimum IN_SET current of $I_{\rm IN_SET(act)}$ is required to turn on the output stage. This feature is implemented to prevent glimming of LEDs caused by leakage currents on the IN_SET pin, see Figure 11 for details. In addition, the IN_SET pin offers the diagnostic feedback information, if the status pin is connected to GND. Another diagnostic possibility is shown in Figure 9, where the diagnosis information is provided via the ST pin (refer to Chapter 7 and Chapter 8) to a micro controller. In case of a fault event with the ST pin connected to GND the IN_SET voltage is increased to $V_{\rm IN_SET(OL/SC)}$ Pos. 8.3.2. Therefore, the device has two voltage domains at the IN_SET-pin, which is shown in Figure 12.



IN_SET Pin

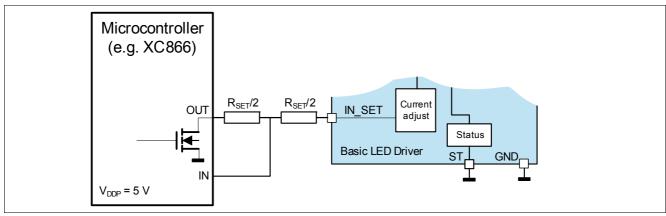


Figure 8 Schematics IN_SET interface to μC, diagnosis via IN_SET pin

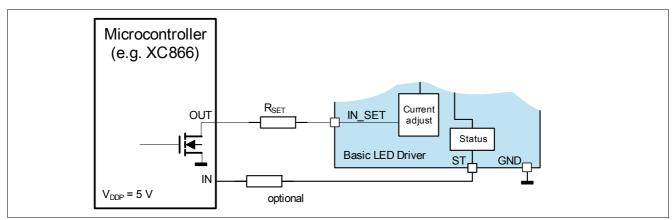


Figure 9 Schematics IN_SET interface to μ C, diagnosis via ST pin

The resulting switching times are shown in Figure 10:

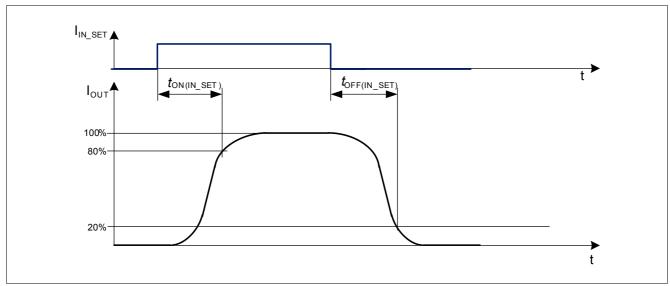


Figure 10 Switching times via IN_SET



IN_SET Pin

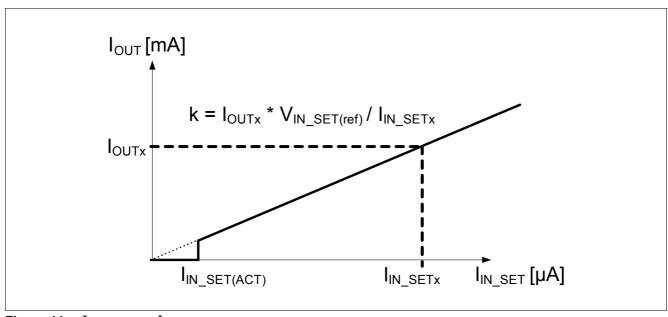


Figure 11 $I_{
m OUT}$ versus $I_{
m INSET}$

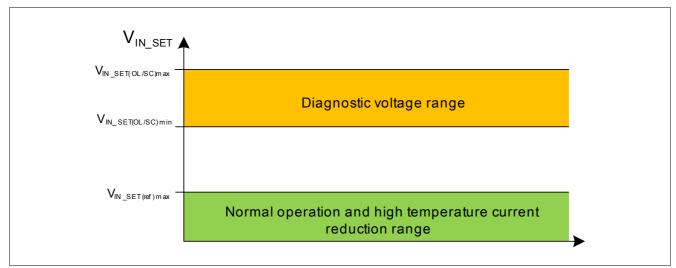


Figure 12 Voltage domains for IN_SET pin, if ST pin is connected to GND



ST Pin

7 ST Pin

The ST pin is a multiple function pin.

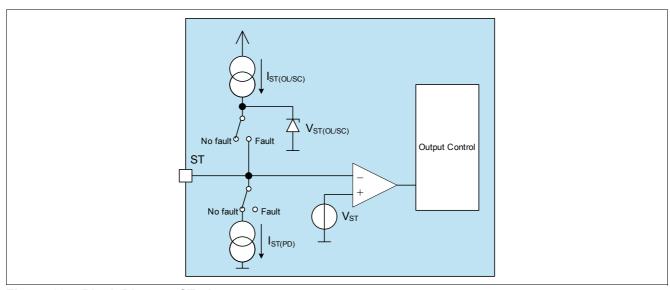


Figure 13 Block Diagram ST pin

7.1 Diagnosis Selector

If the status pin is unconnected or connected to GND via a high ohmic resistor ($V_{\rm ST}$ to be below $V_{\rm ST(L)}$), the ST pin acts as diagnosis output pin. In normal operation (device is activated) the ST pin is pulled to GND via the internal pull down current $I_{\rm ST(PD)}$. In case of an open load or short circuit to GND condition the ST pin is switched to $V_{\rm ST(OL/SC)}$ after the open load or short circuit detection filter time (Pos. 8.3.9, Pos. 8.3.12).

If the device is operated in PWM operation via the VS and/or EN pins the ST pin should be connected to GND via a high ohmic resistor (e.g. $470k\Omega$) to ensure proper device behavior during fast rising VS and/or EN slopes.

If the ST pin is shorted to GND the diagnostic feedback is performed via the IN_SET-pin, which is shown in **Chapter 6.2** and **Chapter 8**.

7.2 Diagnosis Output

If the status pin is unconnected or connected to GND via a high ohmic resistor ($V_{\rm ST}$ to be below $V_{\rm ST(L)}$), it acts as a diagnostic output. In case of a fault condition the ST pin rises its voltage to $V_{\rm ST(OL/SC)}$ (Pos. 8.3.7). Details are shown in Chapter 8.

7.3 Disable Input

If an external voltage higher than $V_{\rm ST(H)}$ (Pos. 8.3.5) is applied to the ST pin, the device is switched off. This function is used for applications, where multiple drivers should be used for one light function. It is possible to combine the drivers' fault diagnosis via the ST pins. If a single LED chain fails, the entire light function is switched off. In this scenario e.g. the diagnostic circuit on the body control module can easily distinguish between the two cases (normal load or load fault), because nearly no current is flowing into the LED module during the fault scenario - the drivers consume a current of $I_{\rm S(fault,STu)}$ (Pos. 5.4.5) or $I_{\rm S(dis,ST)}$ (Pos. 5.4.3).

As soon as one LED chain fails, the ST-pin of this device is switched to $V_{\rm ST(OL/SC)}$. The other devices used for the same light function can be connected together via the ST pins. This leads to a switch off of all devices connected together. Application examples are shown in **Chapter 10**.



ST Pin

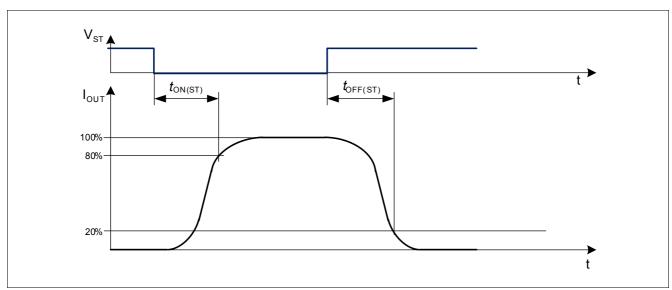


Figure 14 Switching times via ST Pin



8 Load Diagnosis

8.1 Open Load

An open load diagnosis feature is integrated in the TLD1121EL driver IC. If there is an open load on the output, the output is turned off. The potential on the IN_SET pin rises up to $V_{\rm IN_SET(OL/SC)}$. This high voltage can be used as input signal for an μ C as shown in **Figure 9**. The open load status is not latched, as soon as the open load condition is no longer present, the output stage will be turned on again. An open load condition is detected, if the voltage drop over the output stage $V_{\rm PS}$ is below the threshold according **Pos. 8.3.10** and a filter time of $t_{\rm OL}$ is passed.

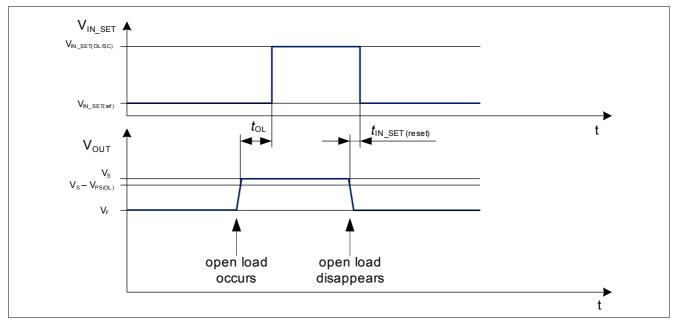


Figure 15 IN_SET behavior during open load condition with ST pin connected to GND



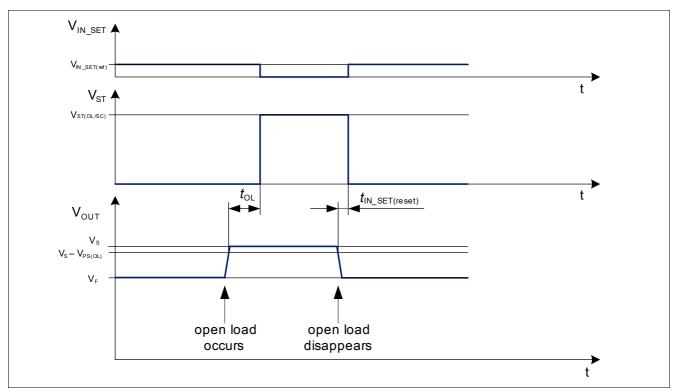


Figure 16 IN_SET and ST behavior during open load condition (ST unconnected)

8.2 Short Circuit to GND detection

The TLD1121EL has an integrated SC to GND detection. If the output stage is turned on and the voltage at the output falls below $V_{\rm OUT(SC)}$ the potential on the IN_SET pin is increased up to $V_{\rm IN_SET(OL/SC)}$ after $t_{\rm SC}$, if the ST pin is connected to GND. If the ST is open or connected to GND via a high ohmic resistor the fault is indicated on the ST pin according to **Chapter 7** after $t_{\rm SC}$. More details are shown in **Figure 18**. This condition is not latched. For detecting a normal condition after a short circuit detection an output current according to $I_{\rm OUT(SC)}$ is driven by the channel.



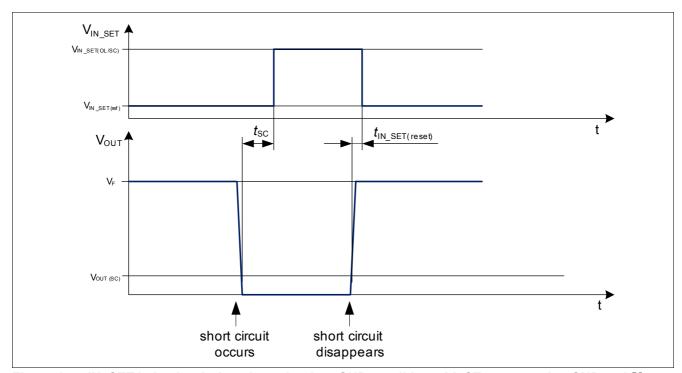


Figure 17 IN_SET behavior during short circuit to GND condition with ST connected to GND and $V_{\rm DEN}$ > $V_{\rm DEN(act)}$

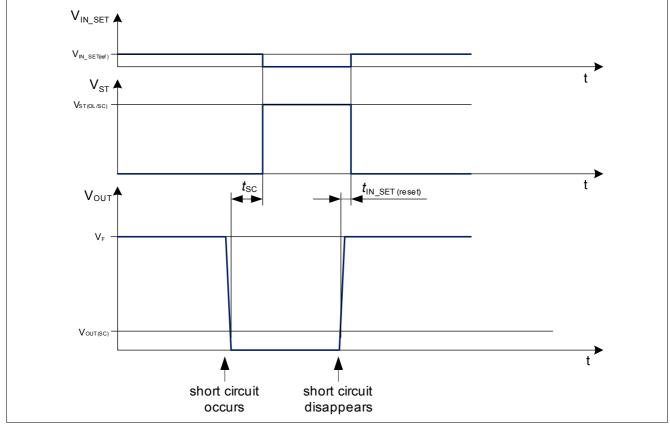


Figure 18 IN_SET and ST behavior during short circuit to GND condition (ST unconnected)



8.3 Electrical Characteristics IN_SET Pin and Load Diagnosis

Electrical Characteristics IN_SET pin and Load Diagnosis

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω , all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Val	ues	Unit	Conditions
			Min.	Тур.	Max.		
8.3.1	IN_SET reference voltage	$V_{IN_SET(ref)}$	1.19	1.23	1.27	V	$^{1)}$ V_{OUT} = 3.6 V T_{j} = 25115 °C
8.3.2	IN_SET open load/short circuit voltage	V _{IN_SET(OL/SC)}	4	-	5.5	V	$V_{\rm S} > 8 \text{ V}$ $V_{\rm j} = 25150 ^{\circ}\text{C}$ $V_{\rm S} = V_{\rm OUT} ^{\circ}(\text{OL}) ^{\circ}\text{OUTx}$ $V_{\rm OUTx} = 0 ^{\circ}\text{C}$
8.3.3	IN_SET open load/short circuit current	$I_{IN_SET(OL/SC)}$	1.5	-	7.4	mA	$^{1)}$ $V_{\rm S}$ > 8 V $T_{\rm j}$ = 25150 °C $V_{\rm IN_SET}$ = 4 V $V_{\rm S}$ = $V_{\rm OUT}$ (OL) or $V_{\rm OUT}$ = 0 V (SC)
8.3.4	ST device turn on threshold (active low) in case of voltage applied from external (ST-pin acting as input)	V _{ST(L)}	0.8	-	-	V	_
8.3.5	ST device turn off threshold (active low) in case of voltage applied from external (ST-pin acting as input)	V _{ST(H)}	_	-	2.5	V	_
8.3.6	ST pull down current	$I_{\mathrm{ST(PD)}}$	_	_	15	μΑ	$V_{\rm EN}$ = 5.5 V $V_{\rm ST}$ = 0.8 V
8.3.7	ST open load/short circuit voltage (ST-pin acting as diagnosis output)	V _{ST(OL/SC)}	4	-	5.5	V	$^{1)}$ $V_{\rm S}$ > 8 V $T_{\rm j}$ = 25150 °C $R_{\rm ST}$ = 470 k Ω $V_{\rm S}$ = $V_{\rm OUT}$ (OL) or $V_{\rm OUT}$ = 0 V (SC)
8.3.8	ST open load/short circuit current (ST-pin acting as diagnosis output)	$I_{\rm ST(OL/SC)}$	100	-	220	μА	$^{1)}$ $V_{\rm S}$ > 8 V $T_{\rm j}$ = 25150 °C $V_{\rm ST}$ = 2.5 V $V_{\rm S}$ = $V_{\rm OUT}$ (OL) or $V_{\rm OUT}$ = 0 V (SC)
8.3.9	OL detection filter time	t_{OL}	10	22	35	μs	$^{1)} V_{\rm S} > 8 \text{ V}$
8.3.10	OL detection voltage $V_{\rm PS(OL)}$ = $V_{\rm S}$ - $V_{\rm OUT}$	$V_{PS(OL)}$	0.2	_	0.4	V	V _S > 8 V
8.3.11	Short circuit to GND detection threshold	$V_{OUT(SC)}$	8.0	_	1.4	V	V _S > 8 V
8.3.12	SC detection filter time	$t_{\rm SC}$	10	22	35	μs	¹⁾ V _S > 8 V



Electrical Characteristics IN_SET pin and Load Diagnosis (cont'd)

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω , all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol		Limit Val	lues	Unit	Conditions
			Min.	Тур.	Max.		
8.3.13	IN_SET diagnosis reset time	$t_{IN_SET(reset)}$	_	5	20	μs	¹⁾ V _S > 8 V
8.3.14	SC detection current in case of unconnected ST-pin	$I_{\mathrm{OUT}(\mathrm{SC},\mathrm{STu})}$	100	200	300	μA	$V_{\rm S}$ > 8 V $V_{\rm OUT}$ = 0 V
8.3.15	SC detection current in case of ST-pin shorted to GND	$I_{OUT(SC,STG)}$	0.1	2	4.75	mA	$V_{\rm S}$ > 8 V $V_{\rm OUT}$ = 0 V $V_{\rm ST}$ = 0 V
8.3.16	IN_SET activation current without turn on of output stage	$I_{IN_SET(act)}$	2	_	15	μA	See Figure 11

¹⁾ Not subject to production test, specified by design



Power Stage

9 Power Stage

The output stage is realized as high side current source with a current of 360 mA. During off state the leakage current at the output stage is minimized in order to prevent a slightly glowing LED.

The maximum current of the channel is limited by the power dissipation and used PCB cooling areas (which results in the applications $R_{th,JA}$).

For an operating current control loop the supply and output voltages according to the following parameters have to be considered:

- Required supply voltage for current control $V_{\rm S(CC)}$, Pos. 5.4.9
- Voltage drop over output stage during current control $V_{PS(CC)}$, Pos. 9.2.6
- Required output voltage for current control $V_{\mathrm{OUT(CC)}}$, Pos. 9.2.7

9.1 Protection

The device provides embedded protective functions, which are designed to prevent IC destruction under fault conditions described in this data sheet. Fault conditions are considered as "outside" normal operating range. Protective functions are neither designed for continuous nor for repetitive operation.

9.1.1 Over Load Behavior

An over load detection circuit is integrated in the LITIXTM Basic IC. It is realized by a temperature monitoring of the output stage (OUT).

As soon as the junction temperature exceeds the current reduction temperature threshold $T_{\rm j(CRT)}$ the output current will be reduced by the device by reducing the IN_SET reference voltage $V_{\rm IN_SET(ref)}$. This feature avoids LED's flickering during static output overload conditions. Furthermore, it protects LEDs against over temperature, which are mounted thermally close to the device. If the device temperature still increases, the output current decreases close to 0 A. As soon as the device cools down the output current rises again.

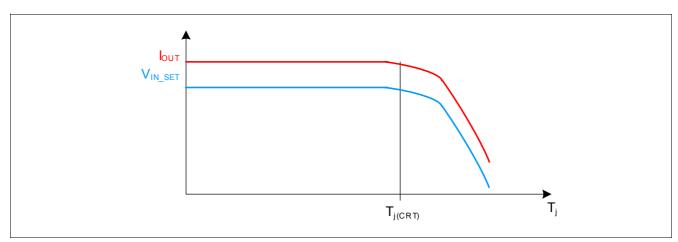


Figure 19 Output current reduction at high temperature

Note: This high temperature output current reduction is realized by reducing the IN_SET reference voltage voltage (Pos.~8.3.1). In case of very high power loss applied to the device and very high junction temperature the output current may drop down to $I_{OUT} = 0$ mA, after a slight cooling down the current increases again.

9.1.2 Reverse Battery Protection

The TLD1121EL has an integrated reverse battery protection feature. This feature protects the driver IC itself, but also connected LEDs. The output reverse current is limited to $I_{\text{OUTx(rev)}}$ by the reverse battery protection.



Power Stage

Note: Due to the reverse battery protection a reverse protection diode for the light module may be obsolete. In case of high ISO-pulse requirements and only minor protecting components like capacitors a reverse protection diode may be reasonable. The external protection circuit needs to be verified in the application.

9.2 Electrical Characteristics Power Stage

Electrical Characteristics Power Stage

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 18 V, $T_{\rm j}$ = -40 °C to +150 °C, $V_{\rm OUT}$ = 3.6 V, all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Тур.	Max.		
9.2.1	Output leakage current	$I_{OUT(leak)}$				μА	$V_{\rm EN}$ = 5.5 V $I_{\rm IN_SET}$ = 0 μ A $V_{\rm OUT}$ = 2.5 V
			_	_	21 9		$T_{\rm j}$ = 150 °C ¹⁾ $T_{\rm j}$ = 85 °C
9.2.2	Output leakage current in boost over battery setup	-I _{OUT(leak,B2B)}	-	-	150	μA	$I_{\rm IN_SET} = 5.5 \text{ V}$ $I_{\rm IN_SET} = 0 \mu\text{A}$ $V_{\rm OUT} = V_{\rm S} = 40 \text{ V}$
9.2.3	Reverse output current	$-I_{ m OUT(rev)}$	_	_	3	μΑ	$^{1)}$ $V_{\rm S}$ = -16 V Output load: LED with break down voltage < - 0.6 V
9.2.4	Output current accuracy limited temperature range	k_{LT}	2092 1935	2250 2250	2408 2565		$^{1)}T_{\rm j}$ = 25115 °C $V_{\rm S}$ = 818 V $V_{\rm PS}$ = 2 V $R_{\rm SET}$ = 612 k Ω $R_{\rm SET}$ = 30 k Ω
9.2.5	Output current accuracy over temperature	k_{ALL}	2092 1935	2250 2250	2408 2565		$T_{\rm j}$ = -40115 °C $V_{\rm S}$ = 818 V $V_{\rm PS}$ = 2 V $R_{\rm SET}$ = 612 kΩ $R_{\rm SET}$ = 30 kΩ
9.2.6	Voltage drop over power stage during current control $V_{\rm PS(CC)} = V_{\rm S} - V_{\rm OUT}$	$V_{PS(CC)}$	0.75	-	-	V	¹⁾ $V_{\rm S}$ = 13.5 V $R_{\rm SET}$ = 12 kΩ $I_{\rm OUT}$ ≥ 90 of $(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.7	Required output voltage for current control	V _{OUT(CC)}	2.3	_	-	V	$I_{\rm S} = 13.5 \text{ V}$ $R_{\rm SET} = 12 \text{ k}\Omega I_{\rm OUT} \ge 90$ of $(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.8	Maximum output current	$I_{ m OUT(max)}$	360	_	_	mA	R_{SET} = 4.7 k Ω The maximum output current is limited by the thermal conditions. Please refer to Pos. 4.3.1 - Pos. 4.3.5



Power Stage

Electrical Characteristics Power Stage (cont'd)

Unless otherwise specified: V_S = 5.5 V to 18 V, T_j = -40 °C to +150 °C, V_{OUT} = 3.6 V, all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Тур.	Max.		
9.2.9	ST turn on time	$t_{ON(ST)}$	_	_	15	μs	$^{2)} V_{\rm S}$ = 13.5 V
							$R_{\rm SET}$ = 12 k Ω
							$ST \rightarrow L$
							$I_{\rm OUT}$ = 80% of
							$(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.10	ST turn off time	$t_{OFF(ST)}$	_	_	10	μs	$^{2)} V_{\rm S} = 13.5 \text{ V}$
							$R_{\text{SET}} = 12 \text{ k}\Omega$
							ST → H
							$I_{\text{OUT}} = 20\% \text{ of}$
0011	IN OFT (4.5		$(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.11	IN_SET turn on time	$t_{ON(IN_SET)}$	_	_	15	μs	$V_{\rm S}$ = 13.5 V
							$I_{IN_SET} = 0 o 100 \ \mu A$ I_{OUT} = 80% of
							$(k_{\text{LT(typ)}}/R_{\text{SET}})$
9.2.12	IN SET turn off time	+			10	μs	$V_{\rm S}$ = 13.5 V
	III_SET turn on time	t _{OFF(IN_SET)}	-	_	10	μδ	$I_{\text{IN SET}}$ = 100 \rightarrow 0 μ A
							$I_{\text{OUT}} = 20\% \text{ of}$
							$(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.13	VS turn on time	t _{ON(VS)}	_	_	20	μs	$V_{\text{EN}} = 5.5 \text{ V}$
		014(V3)					$R_{\rm SET}$ = 12 k Ω
							$V_{\rm S} = 0 \to 13.5 {\rm V}$
							$I_{\rm OUT}$ = 80% of
							$(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.14	Current reduction	$T_{\rm j(CRT)}$	-	140	-	°C	$^{1)}I_{OUT}$ = 95% of
	temperature threshold						$(k_{\rm LT(typ)}/R_{\rm SET})$
9.2.15	Output current during	$I_{OUT(CRT)}$	85% of	_	_	Α	¹⁾ R_{SET} = 12 kΩ
	current reduction at high		$(k_{\rm LT(typ)}/$				$T_{\rm j}$ = 150 °C
	temperature		R_{SET})				

¹⁾ Not subject to production test, specified by design

²⁾ see also Figure 14

³⁾ see also Figure 6



Application Information

10 Application Information

Note: The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device.

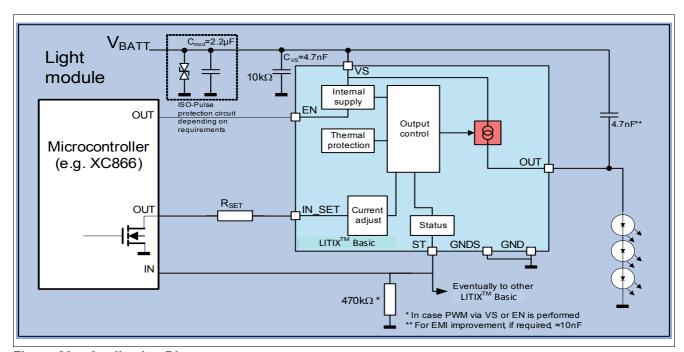


Figure 20 Application Diagram

Note: This is a very simplified example of an application circuit. In case of high ISO-pulse requirements a reverse protection diode may be used for LED protection. The function must be verified in the real application.

10.1 Further Application Information

· For further information you may contact http://www.infineon.com/



Package Outlines

11 Package Outlines

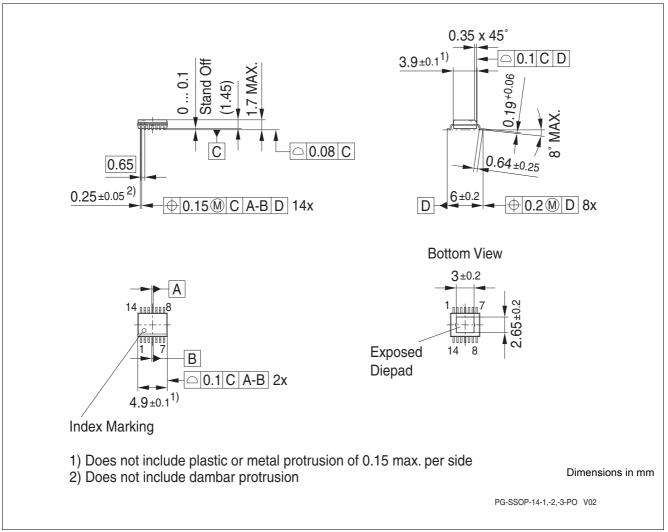


Figure 21 PG-SSOP14

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

For further information on alternative packages, please visit our website: http://www.infineon.com/packages.



Revision History

12 Revision History

Revision	Date	Changes
1.0	2013-08-08	Inital revision of data sheet
1.1	2015-03-19	Updated parameters K _{LT} and K _{ALL} in the chapter Power Stage.

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